<Preliminary Ver.>

UV-A Sensor

GUVV-T13GD-L

Genuine UV Technology

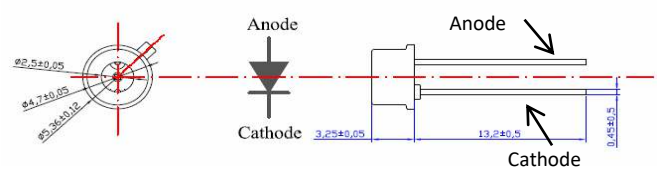
Features

Indium Gallium Nitride Based Material
Schottky-type Photodiode
Photovoltaic Mode Operation
High Responsivity & Low Dark Current

Applications

Full UV Band Monitoring
UV-A Lamp Monitoring
365,385nm UV LED Monitoring

Outline Diagrams and Dimensions



Absolute Maximum Ratings

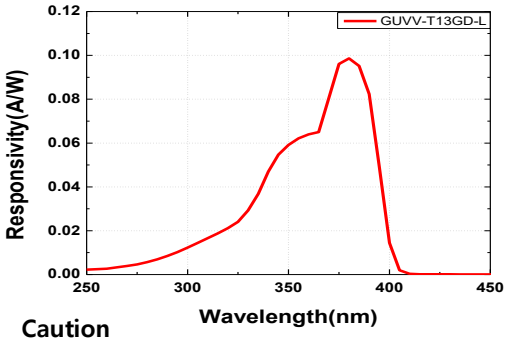
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	℃	
Operating Temperature	T_{op}	-30	85	℃	
Reverse Voltage	$V_{r,\ max.}$		5	V	
Forward Current	$I_{f,max.}$		1	㎃	
Optical Source Power Range	P_{opt}	0.01	100	㎽/㎠	UVA Lamp
Soldering Temperature	T_{sol}		260	℃	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100㎽/㎠.

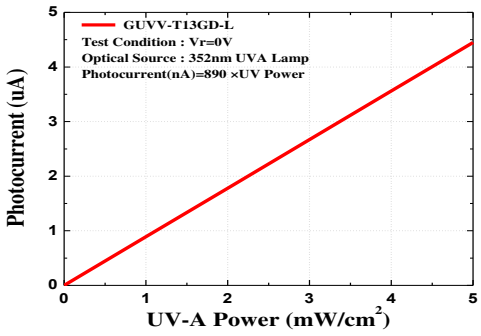
Characteristics (at 25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			20	nA	Vr = 1 V
Photo Current	I_{ph}	801	890	979	nA	UVA Lamp, 1㎽/㎠
Temperature Coefficient	I_{tc}		-0.03		%/℃	UVA Lamp
Responsivity	R		0.098		A/W	λ = 380 ㎚, Vr = 0 V
Spectral Detection Range	λ	295		400	㎚	10% of R
Active area			1.024		㎟	

Responsivity Curve



Photocurrent along UV Power



Caution

ESD can damage the device hence please avoid ESD. Insulate the cap of TO-CAN or it can cause malfunction of the device.